



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 20	0.019 at V _{GS} = - 4.5 V	- 11.4		
	0.025 at V _{GS} = - 2.5 V	- 9.9		
	0.034 at V _{GS} = - 1.8 V	- 8.5		

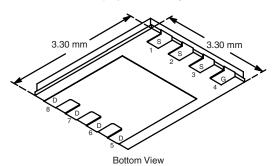
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET: 1.8 V Rated
- New PowerPAK[®] Package
 - Low Thermal Resistance, RthJC
 - Low 1.07 mm Profile





PowerPAK 1212-8

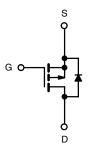


Ordering Information: Si7411DN-T1-E3 (Lead (Pb)-free)

Si7411DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_λ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		٧
Gate-Source Voltage		V _{GS}	± 8		
Continuous Dunin Comment /T 150 9C\d	T _A = 25 °C	- I _D	- 11.4	- 7.5	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 8.2	- 5.4	•
Pulsed Drain Current		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 3	- 1.3	
Mariana Barana Biraha di ad	T _A = 25 °C	P _D	3.6	1.5	W
Maximum Power Dissipation ^a	T _A = 85 °C		1.9	0.8	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian de Ambienta	t ≤ 10 s	- R _{thJA}	28	35	°C/W
Maximum Junction-to-Ambient ^a	Steady State		65	81	
Maximum Junction-to-Case	Steady State	R_{thJC}	2.9	3.8	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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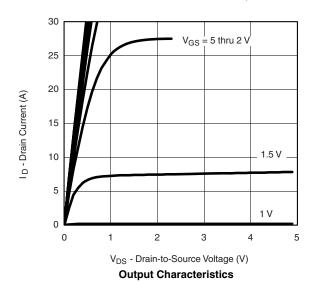
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit
Static	•			•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -300 \mu\text{A}$ - 0.4				٧
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 85 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 30			Α
		V _{GS} = - 4.5 V, I _D = - 11.4 A		0.015	0.019	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 9.9 A		0.020	0.025	Ω
		V _{GS} = - 1.8 V, I _D = - 2.9 A		0.027	0.034	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 11.4 A		35		S
Diode Forward Voltage ^a	V _{SD}	I _S = - 3.0 A, V _{GS} = 0 V		- 0.8	- 1.2	٧
Dynamic ^b						
Total Gate Charge	Q_g			27	41	
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -11.4 \text{ A}$		3.9		nC
Gate-Drain Charge	Q_{gd}			7		
Gate Resistance	R_g	f = 1 MHz		5		Ω
Turn-On Delay Time	t _{d(on)}			23	35	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		45	70	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		135	200	ns
Fall Time	t _f			70	105	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, dl/dt = 100 A/μs		29	50	

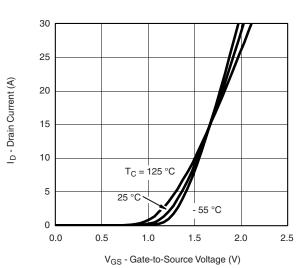
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





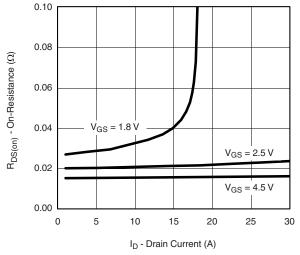
Transfer Characteristics



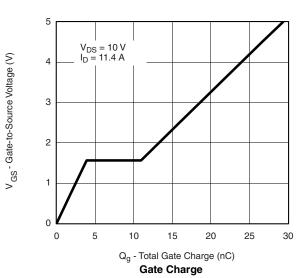


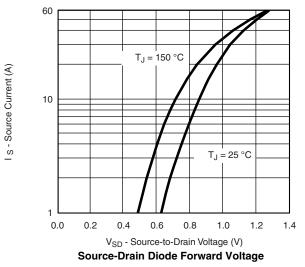


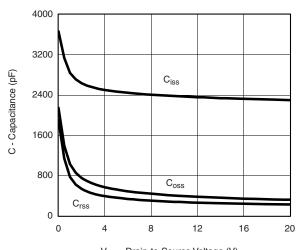
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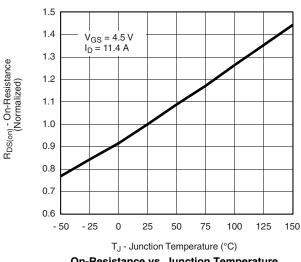
On-Resistance vs. Drain Current



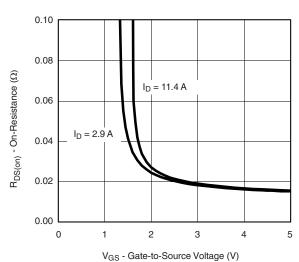




V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

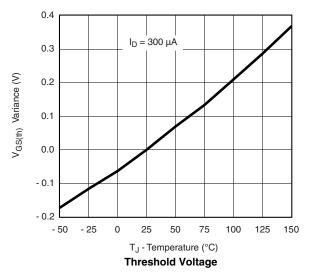


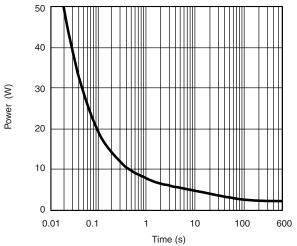
On-Resistance vs. Gate-to-Source Voltage

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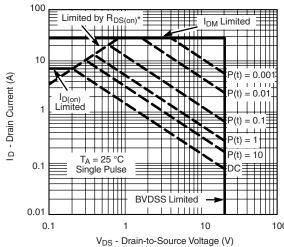
VISHAY

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

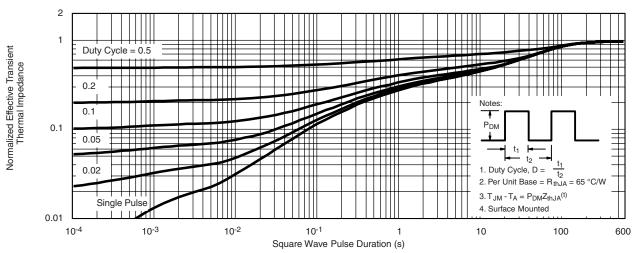




Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified **Safe Operating Area**



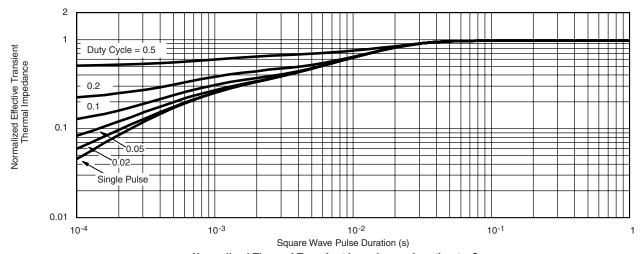
Normalized Thermal Transient Impedance, Junction-to-Ambient





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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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